



DMN6075S-13 Information



For Reference Only

Part Number DMN6075S-13
Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 2A SOT23-3

Package TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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DMN6075S-13 Specifications

Manufacturer Part Number DMN6075S-13 Manufacturer Diodes Incorporated Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-236-3, SC-59, SOT-23-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 12.3nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 606pF @ 20V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 800mW (Ta) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3 Report errors?		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C2A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs12.3nC @ 10VInput Capacitance (Ciss) (Max) @ Vds606pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)800mW (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23Package / CaseTO-236-3, SC-59, SOT-23-3	Package	TO-236-3, SC-59, SOT-23-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C2A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs12.3nC @ 10VInput Capacitance (Ciss) (Max) @ Vds606pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)800mW (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23Package / CaseTO-236-3, SC-59, SOT-23-3	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C2A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs12.3nC @ 10VInput Capacitance (Ciss) (Max) @ Vds606pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)800mW (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23Package / CaseTO-236-3, SC-59, SOT-23-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C2A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs12.3nC @ 10VInput Capacitance (Ciss) (Max) @ Vds606pF @ 20VVgs (Max)±20VFET Feature-Power Dissipation (Max)800mW (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23Package / CaseTO-236-3, SC-59, SOT-23-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 12.3nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 3V @ 250μA 12.3nC @ 10V 10V 8066pF @ 20V +20V FET Feature - Supplier Device Package SOT-23 TO-236-3, SC-59, SOT-23-3	Current - Continuous Drain (Id) @ 25°C	2A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 606pF @ 20V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surface Mount Supplier Device Package Package / Case 606pF @ 20V 606pF @ 20V	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)800mW (Ta)Rds On (Max) @ Id, Vgs85 mOhm @ 3.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23Package / CaseTO-236-3, SC-59, SOT-23-3	Gate Charge (Qg) (Max) @ Vgs	12.3nC @ 10V
FET Feature - Power Dissipation (Max) 800mW (Ta) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3	Input Capacitance (Ciss) (Max) @ Vds	606pF @ 20V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 85 mOhm @ 3.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs85 mOhm @ 3.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23Package / CaseTO-236-3, SC-59, SOT-23-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3	Power Dissipation (Max)	800mW (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3	Rds On (Max) @ Id, Vgs	85 mOhm @ 3.2A, 10V
Supplier Device Package SOT-23 Package / Case TO-236-3, SC-59, SOT-23-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-236-3, SC-59, SOT-23-3	Mounting Type	Surface Mount
	Supplier Device Package	SOT-23
Report errors?	Package / Case	TO-236-3, SC-59, SOT-23-3
		Report errors?

DMN6075S-13 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

DMN6075S-13 Payment Methods



















DMN6075S-13 Shipping Methods













If you have any question about DMN6075S-13, please do not hesitate to contact us!

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